

论文摘要

中国有色金属学报

ZHONGGUO YOUSEJINSHUXUEBAO XUEBAO

第6卷 第2期 (总第19期) 1996年6月

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文章编号: (1996)02-44-3

氮气氛下直拉硅中氮含量的红外光谱测定^①

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摘要: 提出了利用直拉硅中与氮有关的特征红外吸收峰963、996、1081⁻¹及1027cm⁻¹确定直拉硅中氮含量的计算公式并进行了多种样品实测。该法克服了只用963cm⁻¹峰测定直拉硅中氮使结果偏低的弊病, 方法相对偏差为5%~20%。

关键字: 硅 氮 红外吸收光谱法

DETERMING NITROGEN IN CZOCHRALSKI-SILICON BY INFRARED ABSORPTION SPECTROMETRY

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Abstract: The calculation formula for determination of nitrogen in CZ-Si grown under nitrogen atmosphere by infrared absorption lines related to nitrogen at 963, 996, 1 018 and 1 027cm⁻¹ was given and the samples were measured with RSD 5%~20%. This method eliminated the deviation caused by using only 963cm⁻¹ in CZ-Si.

Key words: silicon nitrogen infrared absorption spectrometry

